

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Currently Amended) A semiconductor device comprising:
a semiconductor chip comprising a magnetic element;
an enclosure which seals the ~~magnetic~~ semiconductor chip and has a base material
and a cap material joined together via a sealing material; and

substantially spherical magnetic substance particles which are interspersed in ~~the~~
~~enclosure~~ the base material and the cap material.

2. (Currently Amended) A semiconductor device comprising:
a semiconductor chip comprising a magnetic element;
an enclosure which seals the ~~magnetic~~ semiconductor chip and which has a base
material and a cap material joined together via a sealing material; and
a magnetic film provided on a chip side surface of the base material and on an inner
surface of the cap material so as to surround the semiconductor chip.

3. (Original) The semiconductor device according to claim 1, wherein the enclosure is
a plastic package or a ceramic package.

4. (Original) The semiconductor device according to claim 2, wherein the enclosure is
a ceramic package.

5. (Original) The semiconductor device according to claim 3, wherein the plastic
package contains an epoxy resin or a silicone resin.

6. (Original) The semiconductor device according to claim 3, wherein the ceramic package contains at least one of Al_2O_3 , AlN , and BeO .

7. (Original) The semiconductor device according to claim 4, wherein the ceramic package contains at least one of Al_2O_3 , AlN , and BeO .

8. (Original) The semiconductor device according to claim 1, further comprising a lead frame, and

wherein the lead frame has:

a die pad on which the semiconductor chip is mounted;

an inner lead portion sealed by the enclosure; and

an outer lead portion led out of the enclosure.

9. (Original) The semiconductor device according to claim 2, further comprising a lead frame, and

wherein the lead frame has:

a die pad on which the semiconductor chip is mounted;

an inner lead portion sealed by the enclosure; and

an outer lead portion led out of the enclosure.

10. (Original) The semiconductor device according to claim 8, wherein the inner lead portion of the lead frame has a stacked structure in which a plurality of conductive layers are stacked via insulating layers, and the plurality of conductive layers are electrically connected to corresponding external connection electrodes on the semiconductor chip by bonding wires.

11. (Original) The semiconductor device according to claim 9, wherein the inner lead portion of the lead frame has a stacked structure in which a plurality of conductive layers are

stacked via insulating layers, and the plurality of conductive layers are electrically connected to corresponding external connection electrodes on the semiconductor chip by bonding wires.

12. (Original) The semiconductor device according to claim 1, wherein the magnetic element is a tunnel magneto-resistance element.

13. (Original) The semiconductor device according to claim 2, wherein the magnetic element is a tunnel magneto-resistance element.

14. (Original) The semiconductor device according to claim 1, wherein each magnetic substance particle contains at least one of an insulator, an oxide, and a ferrite.

15. (Original) The semiconductor device according to claim 1, wherein each magnetic substance particle has a diameter of 20 μm or less.

16. (Original) The semiconductor device according to claim 1, wherein the magnetic substance particles occupy 1 wt% or more of the enclosure.

17. (New) A semiconductor device comprising:
a semiconductor chip comprising a magnetic element;
an enclosure which seals the magnetic chip; and
substantially spherical magnetic substance particles which are interspersed in the enclosure, the particles preventing magnetic shape anisotropy.

18. (New) The semiconductor device according to claim 17, wherein the enclosure is a plastic package or a ceramic package.

19. (New) The semiconductor device according to claim 17, wherein the magnetic element is a tunnel magneto-resistance element.

20. (New) The semiconductor device according to claim 17, wherein each magnetic substance particle contains at least one of an insulator, an oxide, and a ferrite.